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APR 23 2004

OFFICIAL

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of: Anthony *et al.*

Docket: TI-24953

Serial No.: 09/116,138

Examiner: W. D. Coleman

Filed: 07/15/98

Art Unit: 2823

For: High Permittivity Silicate Gate Dielectric

FACSIMILE CERTIFICATE

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David Denker, Reg. No. 40,987

FACSIMILE COVER SHEET

<input checked="" type="checkbox"/> FACSIMILE COVER SHEET (1 SHEET)	<input checked="" type="checkbox"/> AMENDMENT <u>1,111 w/ 2 mo EOT (3 pages)</u>
<input type="checkbox"/> NEW APPLICATION	<input type="checkbox"/> EOT <u>(# Pages)</u>
<input type="checkbox"/> DECLARATION	<input type="checkbox"/> NOTICE OF APPEAL <u>(# Pages)</u>
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<input type="checkbox"/> FORMAL DRAWINGS	<input type="checkbox"/> ISSUE FEE
<input type="checkbox"/> INFORMAL DRAWINGS	<input type="checkbox"/> REPLY BRIEF (IN TRIPLICATE)
<input type="checkbox"/> CONTINUATION APP'N	<input checked="" type="checkbox"/> Interview Summary
<input type="checkbox"/> DIVISIONAL APP'N	
NAME OF INVENTOR(S): Anthony <i>et al.</i>	
TITLE OF INVENTION: High Permittivity Silicate Gate Dielectric	
TI FILE NO.: TI-24953	DEPOSIT ACCT. NO.: 20-0668
FAXED: April 23, 2004 DUE: March 16, 2004 ATTY/SEC'Y: DD/tms	
RECEIPT DATE & SERIAL NO.: Appl. No.: 09/116,138 Filing Date: 07/15/98	

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INTERVIEW SUMMARY

April 14, 2004

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

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Examiner:

This is a summary of the interview between Examiner David Coleman and Applicants' attorney, David Denker on March 16, 2004. The interview discussed the prior art rejection over Hsieh '035. Examiner requested that Applicants clearly limit the claims to methods of making transistors—as opposed to Hsieh '035's methods of fabricating capacitors. I agreed to more clearly limit the claims to methods of making transistors.

Additionally, I requested rejoinder of claims 28 and 29, (which depend from claim 27), as well as claims 46 and 71 - 73. Claim 46 is similar to claim 1, but has a zirconium silicate dielectric layer limitation. Claim 46's dependent claim 71 is similar to claim 26. Examiner indicated that he would rejoin the claims.

Respectfully submitted,


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